

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-344594

(43)Date of publication of application : 12.12.2000

(51)Int.Cl.

C30B 15/10
C30B 29/06

(21)Application number : 11-158401

(71)Applicant : SUMITOMO METAL IND LTD

(22)Date of filing : 04.06.1999

(72)Inventor : INOUE KUNIHARU

INOUE JIRO

ONISHI HAJIME

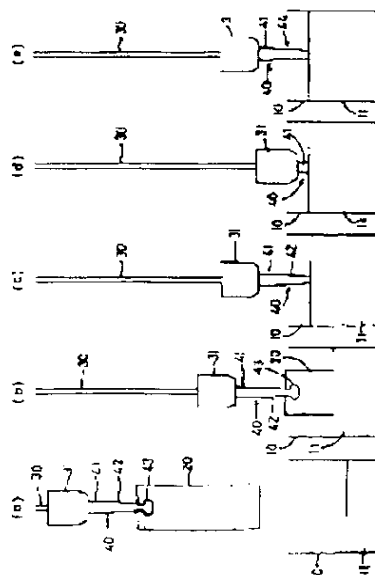
YAMAMOTO KIRIO

(54) METHOD FOR SUPPLYING SILICON RAW MATERIAL AND PRODUCTION OF SINGLE CRYSTAL SILICON

(57)Abstract:

PROBLEM TO BE SOLVED: To improve production efficiency when a single crystal is produced by an additional charge or recharge method and to suppress the formation of unfused parts from rod-shaped polycrystalline silicon supplied by the additional charge or recharge method.

SOLUTION: When rod-shaped polycrystalline silicon 20 is additionally supplied from the upper part to silicon molten liquid 11 in a crucible 10, the polycrystalline silicon 20 is directly held by a seed crystal 40. Then, after allowing the polycrystalline silicon 20 to fall down and supplying the whole of the polycrystalline silicon 20 to the silicon molten liquid 11, a single crystal 44 is pulled up while successively using the seed crystal 40.



LEGAL STATUS

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than

CR Dovetail w/Saw Cut

(7 March, 1997)

R1 = 3/64 inch per DWG 5-M-01005

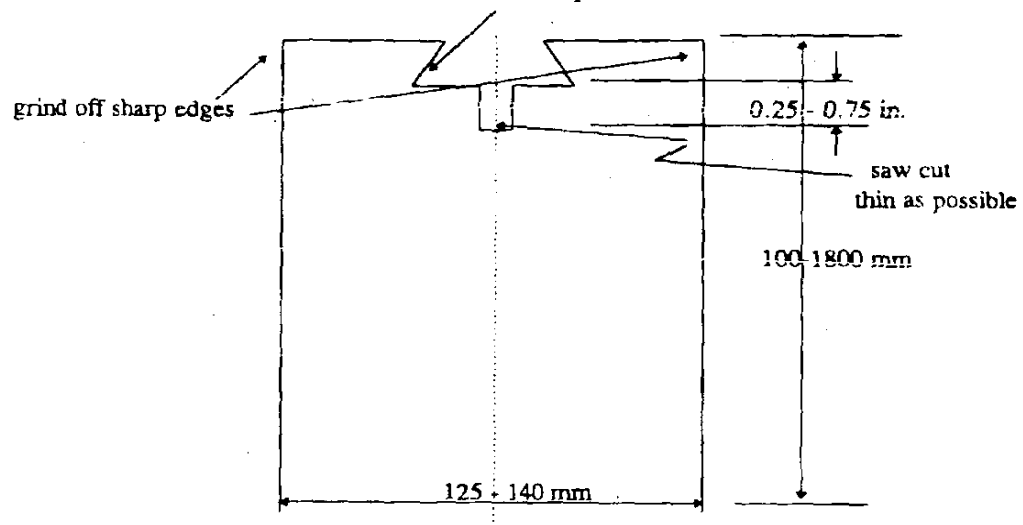


Figure 1